



Bipolar NPN Bare Die – BTN6176

Part Description

The BTN6176 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 50V
- VCEO = 20V
- VEBO = 7V
- hFE = 230-600 @ VCE = 2V, IC = 0.5A
- VCE(Sat) = 1V @ IC = 3A, IB = 100mA
- fT = 150 MHz @ VCE = 6V, IE = 0A
- COBO = 50pF @ VCB = 10V

Features

Low VCE(sat)

Die Size (Unawn)

1020 μ m X 1020 μ m, 40 Mils X 40 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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